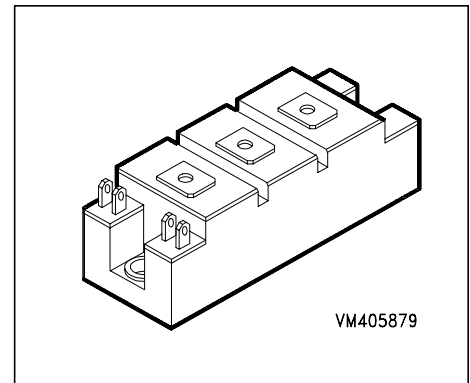


IGBT Power Module

Preliminary data

- Half-bridge
- Including fast free-wheeling diodes
- Package with insulated metal base plate
- $R_{G\ on,min} = 27\ \Omega$



| Type | V_{CE} | I_C | Package | Ordering Code |
|-------------------|----------|-------|---------------|------------------|
| BSM 50 GB 170 DN2 | 1700V | 72A | HALF-BRIDGE 1 | C67070-A2701-A67 |

Maximum Ratings

| Parameter | Symbol | Values | Unit |
|---|-------------|---------------|------------|
| Collector-emitter voltage | V_{CE} | 1700 | V |
| Collector-gate voltage | V_{CGR} | 1700 | |
| $R_{GE} = 20\ k\Omega$ | | | |
| Gate-emitter voltage | V_{GE} | ± 20 | |
| DC collector current | I_C | | A |
| $T_C = 25\ ^\circ C$ | | 72 | |
| $T_C = 80\ ^\circ C$ | | 50 | |
| Pulsed collector current, $t_p = 1\ ms$ | I_{Cpuls} | | |
| $T_C = 25\ ^\circ C$ | | 144 | |
| $T_C = 80\ ^\circ C$ | | 100 | |
| Power dissipation per IGBT | P_{tot} | | W |
| $T_C = 25\ ^\circ C$ | | 500 | |
| Chip temperature | T_j | + 150 | $^\circ C$ |
| Storage temperature | T_{stg} | -55 ... + 150 | |
| Thermal resistance, chip case | R_{thJC} | ≤ 0.25 | K/W |
| Diode thermal resistance, chip case | R_{thJCD} | ≤ 0.75 | |
| Insulation test voltage, $t = 1\ min.$ | V_{is} | 4000 | Vac |
| Creepage distance | - | 20 | mm |
| Clearance | - | 11 | |
| DIN humidity category, DIN 40 040 | - | F | - |
| IEC climatic category, DIN IEC 68-1 | - | 55 / 150 / 56 | |

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

Static Characteristics

| | | | | | |
|--|---------------|--------|------------|------------|----|
| Gate threshold voltage $V_{GE} = V_{CE}, I_C = 4\text{ mA}$ | $V_{GE(th)}$ | 4.8 | 5.5 | 6.2 | V |
| Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_j = 125\text{ °C}$ | $V_{CE(sat)}$ | - - | 3.4 4.6 | 3.9 5.3 | |
| Zero gate voltage collector current $V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$ | I_{CES} | - - | 0.4 1.6 | 0.5 - | mA |
| Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | - | - | 320 | nA |

AC Characteristics

| | | | | | |
|---|-----------|----|------|---|----|
| Transconductance $V_{CE} = 20\text{ V}, I_C = 50\text{ A}$ | g_{fs} | 18 | - | - | S |
| Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{iss} | - | 8 | - | nF |
| Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{oss} | - | 0.64 | - | |
| Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{rss} | - | 0.25 | - | |

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

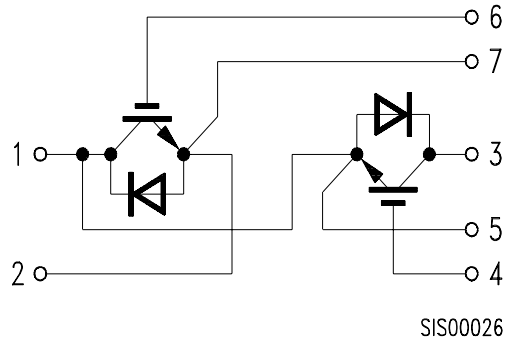
Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

| | | | | | |
|--|--------------|---|-----|------|----|
| Turn-on delay time $V_{CC} = 1200\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$ $R_{Gon} = 27\ \Omega$ | $t_{d(on)}$ | - | 350 | 700 | ns |
| Rise time $V_{CC} = 1200\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$ $R_{Gon} = 27\ \Omega$ | t_r | - | 150 | 300 | |
| Turn-off delay time $V_{CC} = 1200\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 50\text{ A}$ $R_{Goff} = 27\ \Omega$ | $t_{d(off)}$ | - | 650 | 1000 | |
| Fall time $V_{CC} = 1200\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 50\text{ A}$ $R_{Goff} = 27\ \Omega$ | t_f | - | 90 | 140 | |

Free-Wheel Diode

| | | | | | |
|---|----------|---|------------|----------|---------------|
| Diode forward voltage $I_F = 50\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 50\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$ | V_F | - | 2.3 2.1 | 2.8 - | V |
| Reverse recovery time $I_F = 50\text{ A}$, $V_R = -1200\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -600\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$ | t_{rr} | - | 0.3 | - | μs |
| Reverse recovery charge $I_F = 50\text{ A}$, $V_R = -1200\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -600\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$ | Q_{rr} | - | 4 12 | - - | μC |

Circuit Diagram



Package Outlines

Dimensions in mm

Weight: 250 g

